

## **In the Claims**

Amend claims 1 and 4-9, and add new claims 10-11 as follows:

1. (Currently Amended) A method of forming a printed circuit board, the method comprising the steps of:

providing a substrate comprising a seed layer formed by electroless plating;

forming a masking layer on said seed layer to provide first regions of exposed seed layer;

forming a circuit pattern on said first regions of exposed seed layer by electrolytic plating;

removing said masking layer to expose second regions of said seed layer; and

simultaneously exposing said circuit pattern and said exposed second regions of said seed layer to an etching liquid at a temperature less than about 15 degrees Celcius, and etching with said etching liquid said exposed second regions at a first etch rate and said circuit pattern at a second etch rate different than said first etch rate ~~etching said exposed second regions of said seed layer with an etching liquid, said etching liquid at a temperature less than about 15 degrees Celcius.~~

2. (Original) The method of claim 1, wherein the temperature of said etching liquid is about 5°C to about 10°C.

3. (Original) The method of claim 1, wherein said masking layer comprises photoresist.

4. (Currently Amended) The method of claim 1, wherein said seed layer and said circuit pattern comprise copper.

5. (Currently Amended) The method of claim 1, wherein a distance between confronting portions of said circuit pattern is about 150µm or less.

6. (Currently Amended) The method of claim 1, wherein said seed layer and said circuit pattern are formed by copper plating.

7. (Currently Amended) The method of claim 1, wherein said etching liquid comprises an acid.

8. (Currently Amended) The method of claim 7, wherein said acid comprises an  $\text{H}_2\text{O}_2\text{-H}_2\text{SO}_4$  aqueous solution.

9. (Currently Amended) The method of claim 1, wherein said substrate is dipped in said etching liquid within a dip bath.

10. (New) The method of claim 1, wherein said first etch rate is greater than said second etch rate.

11. (New) The method of claim 1, wherein the temperature of said etching liquid is greater than 5 degrees Celcius and less than about 15 degrees Celcius.